



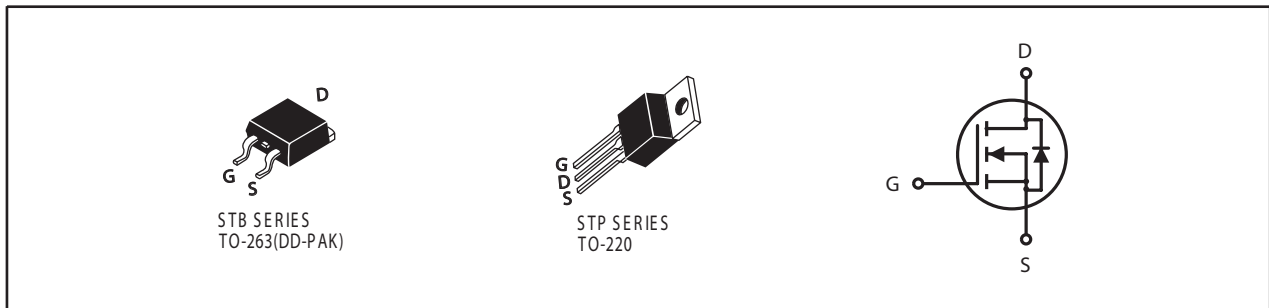
N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

VDSS	ID	RDS(ON) (mΩ) Typ
60V	65A	15 @ VGS=10V

FEATURES

- Super high dense cell design for extremely low RDS(ON).
- High power and current handling capability.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	65
		T _C =70°C	54
I _{DM}	-Pulsed ^b	190	A
E _{AS}	Avalanche Energy ^d	156	mJ
P _D	Maximum Power Dissipation ^a	T _C =25°C	125
		T _C =70°C	87.5
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 175	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	1.2	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body leakage current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	2.8	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =32.5A		15	19	m ohm
g _{FS}	Forward Transconductance	V _{DS} =20V , I _D =32.5A		48		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		2300		pF
C _{OSS}	Output Capacitance			142		pF
C _{RSS}	Reverse Transfer Capacitance			108		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On DelayTime	V _{DD} =30V I _D =1A V _{GS} =10V R _{GEN} =60 ohm		63		ns
t _r	Rise Time			71		ns
t _{D(OFF)}	Turn-Off DelayTime			162		ns
t _f	Fall Time			42		ns
Q _g	Total Gate Charge	V _{DS} =30V, I _D =25A, V _{GS} =10V		28		nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V, I _D =25A, V _{GS} =10V		5		nC
Q _{gd}	Gate-Drain Charge			11		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A		0.75	1.3	V

Notes

- a. Surface Mounted on FR4 Board, t ≤ 10sec.
- b. Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- c. Guaranteed by design, not subject to production testing.
- d. Starting T_J=25°C, L=0.5mH, V_{DD} = 30V. (See Figure13)

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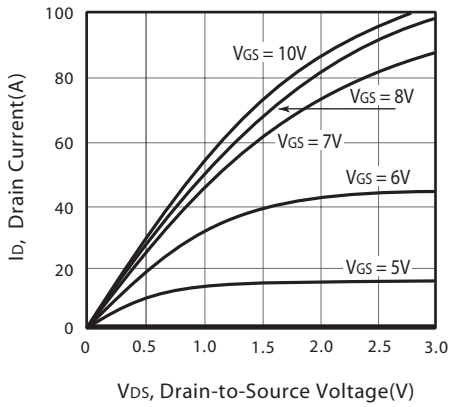


Figure 1. Output Characteristics

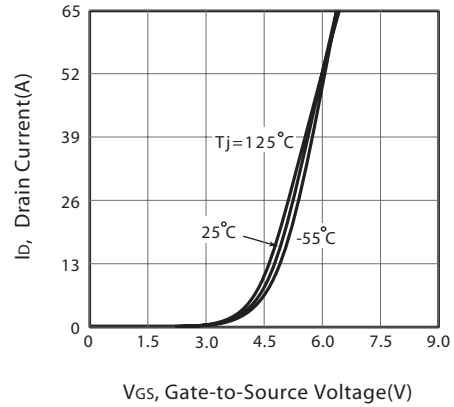


Figure 2. Transfer Characteristics

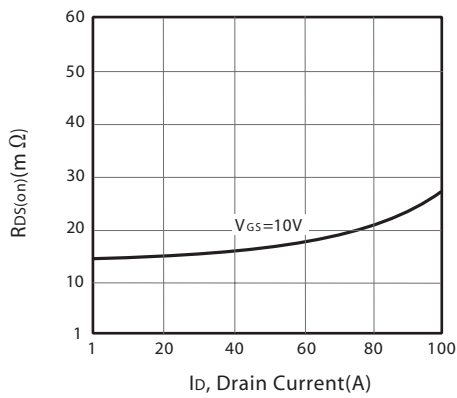


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

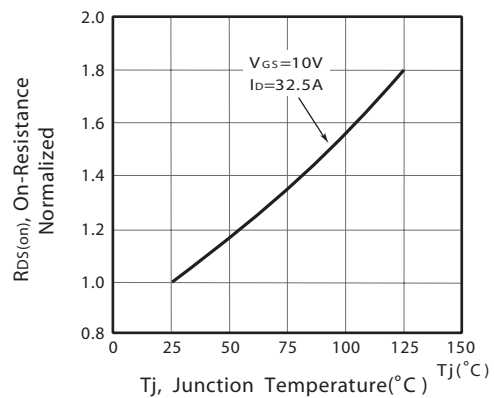


Figure 4. On-Resistance Variation with Drain Current and Temperature

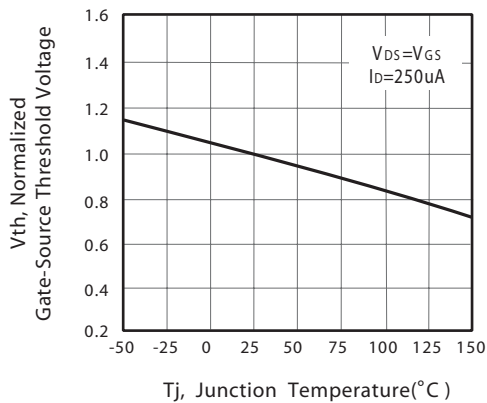


Figure 5. Gate Threshold Variation with Temperature

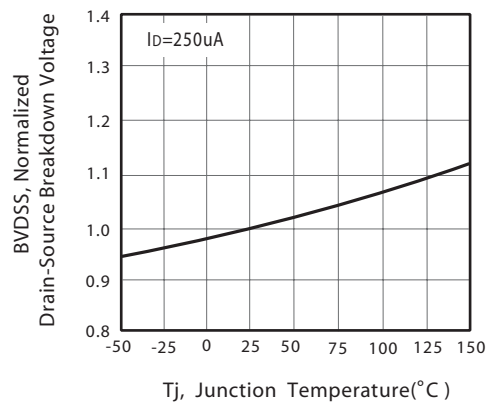


Figure 6. Breakdown Voltage Variation with Temperature

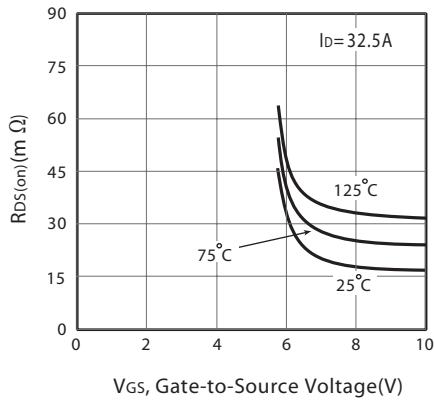


Figure 7. On-Resistance vs. Gate-Source Voltage

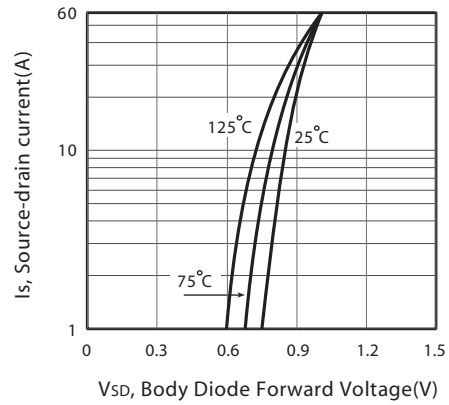


Figure 8. Body Diode Forward Voltage Variation with Source Current

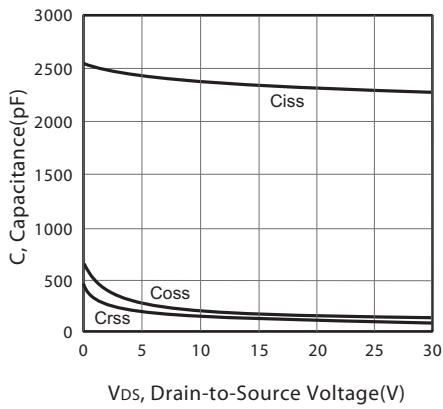


Figure 9. Capacitance

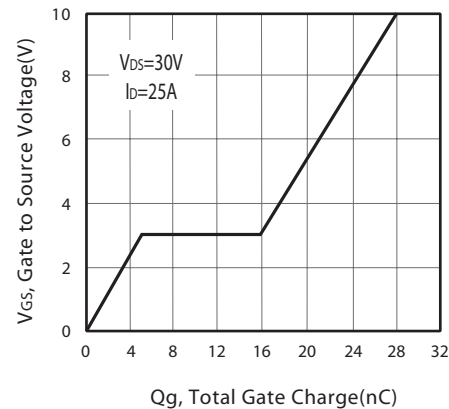


Figure 10. Gate Charge

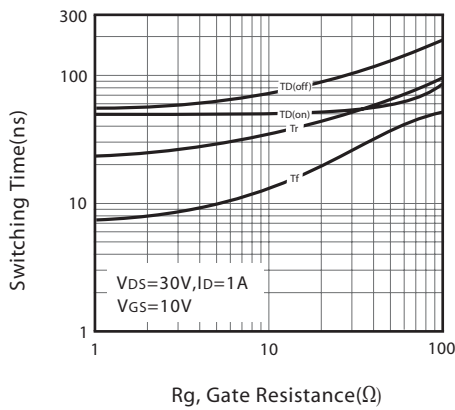


Figure 11. switching characteristics

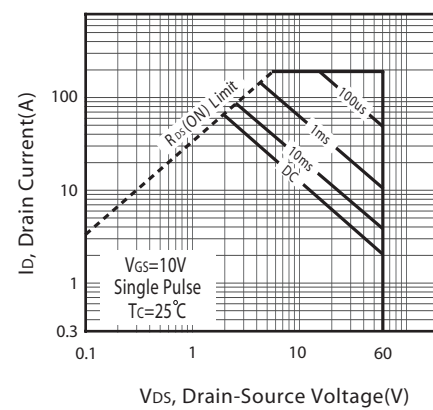
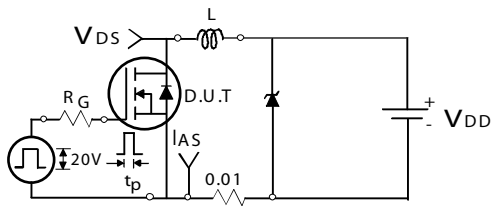
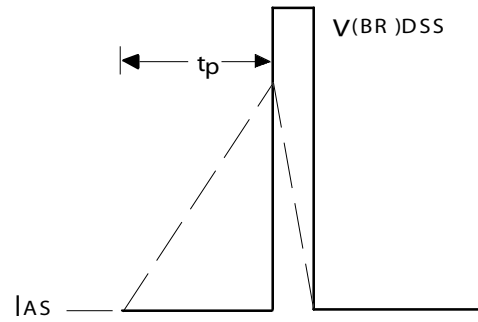


Figure 12. Maximum Safe Operating Area



Unclamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

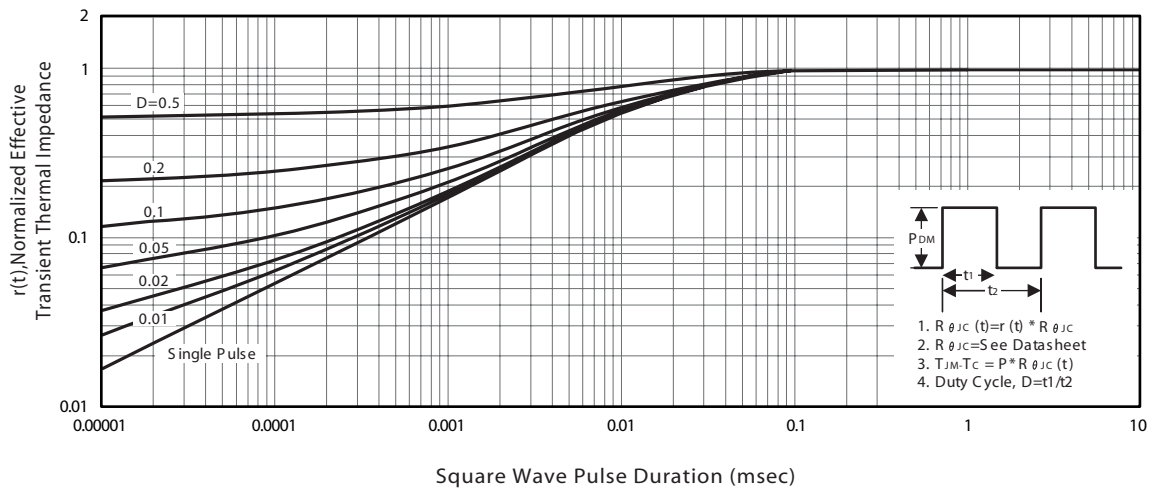


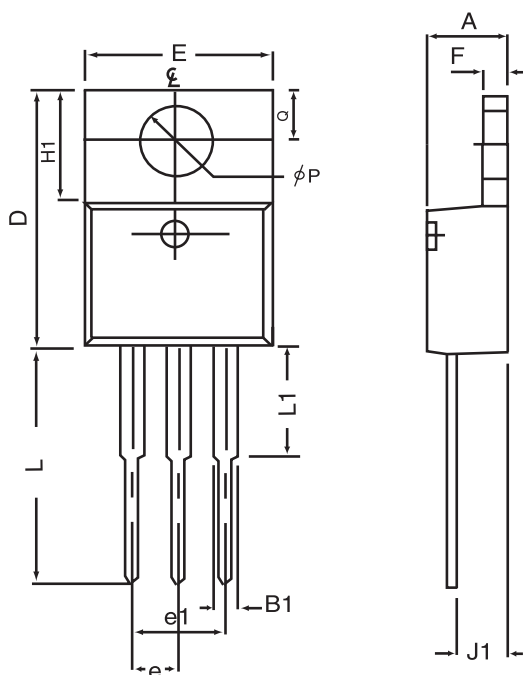
Figure 14. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

TO-220

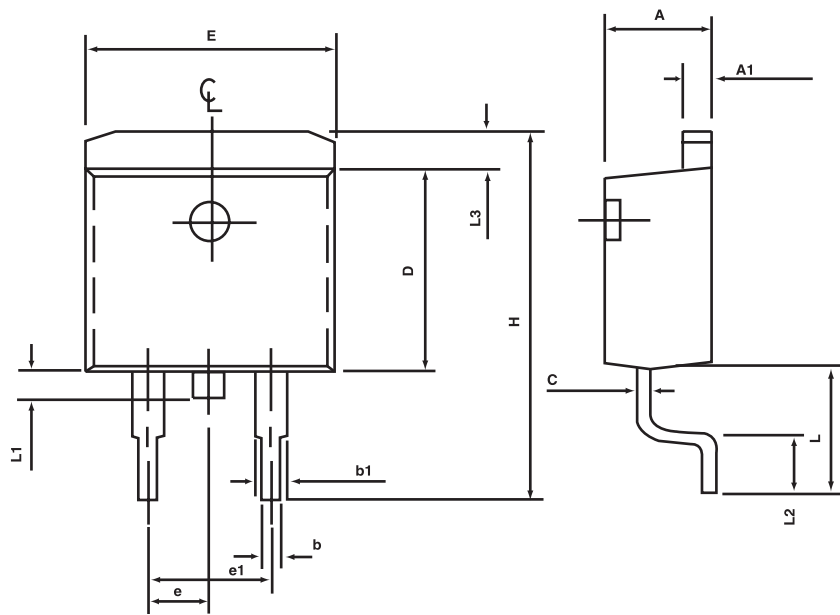


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	4.80	0.170	0.189
B1	1.27	1.65	0.050	0.630
D	14.6	16.00	0.575	0.610
E	9.70	10.41	0.382	0.410
e	2.34	2.74	0.092	0.108
e1	4.68	5.48	0.184	0.216
F	1.14	1.40	0.045	0.055
H1	5.97	6.73	0.235	0.265
J1	2.20	2.79	0.087	0.110
L	12.88	14.22	0.507	0.560
L1	3.00	6.35	0.120	0.250
φP	3.50	3.94	0.138	0.155
Q	2.54	3.05	0.100	0.120

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PACKAGE OUTLINE DIMENSIONS

TO-263AB



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
A1	1.22	1.32	0.048	0.055
b	0.69	0.94	0.027	0.037
b1	1.22	1.40	0.048	0.055
C	0.36	0.56	0.014	0.022
D	8.64	9.652	0.340	0.380
E	9.70	10.54	0.382	0.415
e	2.29	2.79	0.090	0.110
e1	4.83	5.33	0.190	0.210
H	14.60	15.78	0.575	0.625
L	4.70	5.84	0.185	0.230
L1	1.20	1.778	0.047	0.070
L2	2.24	2.84	0.088	0.111
L3	1.40 MAX		0.055 MAX	